

Sheet 1 of 2

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 118072		APPLICATION NO. 10/733,455	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT Masahiro KANAI			
				FILING DATE December 12, 2003			
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EXAMINER

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